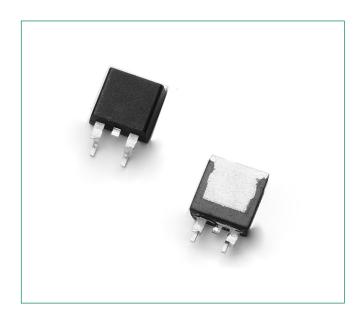


# Surface Mount - 400V - 800V > MCR12DCM, MCR12DCN

# MCR12DCM, MCR12DCN





**Description** 

This thyristor is designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gatecontrolled devices are needed.

#### **Features**

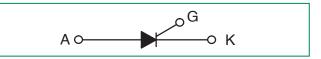
- Small Size
- Passivated Die for Reliability and Uniformity
- Low Level Triggering and Holding Characteristics
- Epoxy Meets rating UL Recognized compound meets flammability rating V-0.
- ESD Ratings: Human Body Model, 3B > 8000 V Machine Model, C > 400 V
- Pb-Free Packages are Available

## **Pin Out**





# **Functional Diagram**



#### **Additional Information**









## **Maximum Ratings** $(T_j = 25^{\circ}C \text{ unless otherwise noted})$

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1)	MCR12DCM	V <sub>DRM</sub>	600	V
(– 40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)	MCR12DCN	V <sub>RRM</sub>	800	V
On-State RMS Current (180° Conduction Angles; T <sub>c</sub> = 90°C)		T (RMS)	12	А
Average On-State Current (180° Conduction Angles; T <sub>c</sub> = 90°C)		I <sub>T(AV)</sub>	7.8	А
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, $T_J = 125$ °C)		I <sub>TSM</sub>	100	А
Circuit Fusing Consideration (t = 8.3 ms)		l²t	41	A²sec
Forward Peak Gate Power (Pulse Width $\leq$ 10 $\mu$ sec, $T_{\rm C} = 90^{\circ}$ C)		P <sub>GM</sub>	5.0	W
Forward Average Gate Power (t = 8.3 msec, $T_c$ = 90°C)		P <sub>GM (AV)</sub>	0.5	W
Forward Peak Gate Current (Pulse Width $\leq$ 1.0 $\mu$ sec, $T_c$ = 90°C)		  GM	2.0	А
Operating Junction Temperature Range		T <sub>J</sub>	-40 to 110	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to 150	°C

Maximum ratings are those values beyond which component damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, component functional operation is not implied, damage may occur and reliability may be affected.

#### **Thermal Characteristics**

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R <sub>eJC</sub>	2.2	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	88	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	R <sub>eJA</sub>	80	
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T <sub>L</sub>	260	°C

<sup>1.</sup> V<sub>DBM</sub> and V<sub>RBM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

# **Thyristors**

# **Electrical Characteristics** - **OFF** $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Forward or Reverse Blocking Current (V <sub>AK</sub> = Rated V <sub>DBM</sub> or V <sub>RBM</sub> Gate Open)	$T_{_{\rm J}}=25^{\circ}{\rm C}$	l <sub>DRM</sub>	-	-	0.01	mA
(V <sub>AK</sub> = Hated V <sub>DRM</sub> Of V <sub>RRM</sub> date Open)	T <sub>J</sub> = 125°C	I <sub>RRM</sub>	-	-	5.0	l IIIA

# **Electrical Characteristics** • **ON** (T<sub>J</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Forward On–State Voltage (Note 2) ( $I_{TM} = 16 \text{ A}$ )		V <sub>TM</sub>	-	1.3	1.9	V
Gate Trigger Current (Continuous dc)	T <sub>J</sub> = 25°C	l I <sub>GT</sub>	2.0	7.0	20	mA
$(V_D = 12 \text{ V}; R_L = 100 \Omega)$	$T_J = -40$ °C	'GT	-	-	40	111/4
Gate Trigger Voltage (Continuous dc)	T <sub>J</sub> = 25°C	V	0.5	0.65	1.0	V
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	$T_J = -40$ °C	V <sub>GT</sub>	-	_	2.5	
Gate Non-Trigger Voltage (V <sub>D</sub> = 12 V, R <sub>L</sub> = 100 Ω)	T <sub>J</sub> = 125°C	V <sub>GD</sub>	0.2	-	-	V
Holding Current	T <sub>J</sub> = 25°C		4.0	22	40	mA
(V <sub>D</sub> = 12 V, Gate Open, Initiating Current = 200 mA)	$T_J = -40$ °C	I <sub>H</sub>	-	-	80	
Latch Current $(V_D = 12 \text{ V}, I_G = 20 \mu$	A, T <sub>J</sub> = 25°C)		4.0	22	40	mA
$(V_D = 12 \text{ V, I}_G = 40 \mu\text{M})$	A, T <sub>J</sub> = -40°C)		-	-	80	IIIA

## **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Off–State Voltage $(V_D = Rated V_{DRM} Exponential Waveform, Gate Open, T_J = 125°C)$	dv/dt	50	200	-	V/µs

<sup>2.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

<sup>3. 1/8&</sup>quot; from case for 10 seconds.

<sup>4.</sup> Pulse Test: Pulse Width  $\leq$  2.0 msec, Duty Cycle  $\leq$  2%.



## **Voltage Current Characteristic of SCR**

Symbol	Parameter	
$V_{DRM}$	Peak Repetitive Forward Off State Voltage	
I <sub>DRM</sub>	Peak Forward Blocking Current	
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage	
l <sub>RRM</sub>	Peak Reverse Blocking Current	
V <sub>TM</sub>	Maximum On State Voltage	
I <sub>H</sub>	Holding Current	

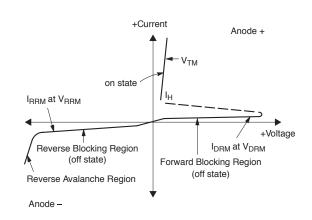


Figure 1. Average RMS Current Derating

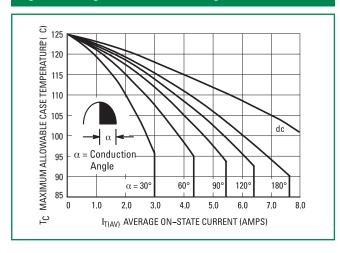


Figure 2. On-State Power Dissipation

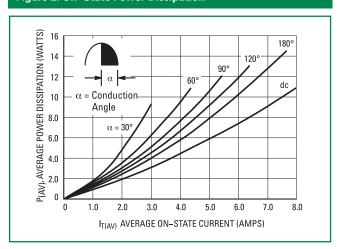
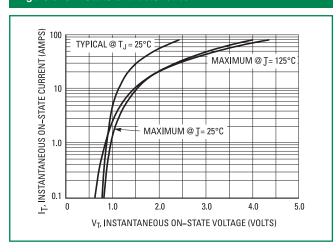


Figure 3. On-State Characteristics



**Figure 4. Transient Thermal Response** 

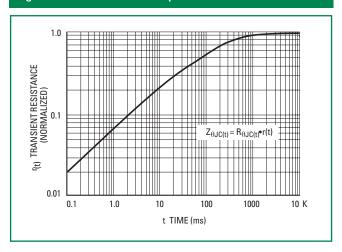




Figure 5. Typical Gate Trigger Current vs Junction Temperature

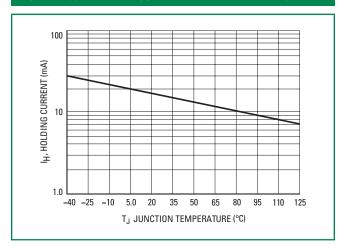


Figure 6. Typical Gate Trigger Voltage vs Junction Temperature

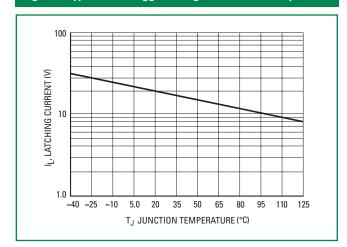


Figure 7. Typical Holding Current vs Junction Temperature

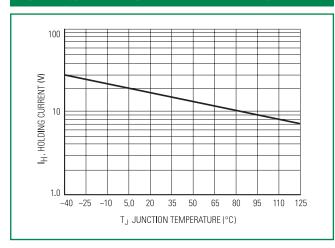


Figure 7. Typical Holding Current vs Junction Temperature

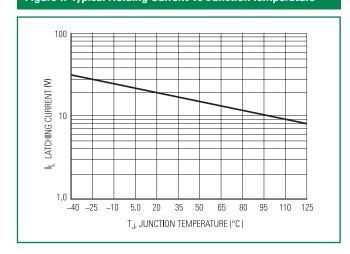
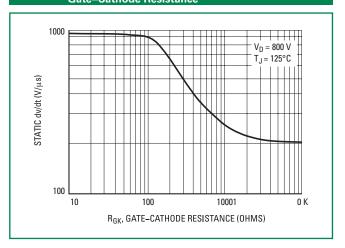
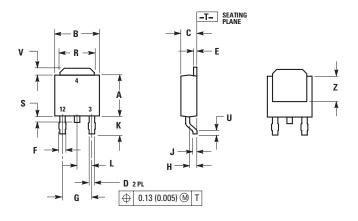


Figure 9. Exponential Static dv/dt vs Gate-Cathode Resistance



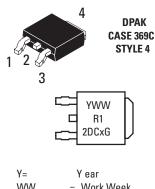
#### **Dimensions**



<u> </u>	Inches		Millim	neters	
Dim	Min	Max	Min	Max	
А	0.235	0.245	5.97	6.22	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
Е	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.180 BSC		4.58 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
K	0.102	0.114	2.60	2.89	
L	0.090 BSC		2.29	BSC	
R	0.180	0.215	4.57	5.45	
S	0.025	0.040	0.63	1.01	
U	0.020		0.51		
V	0.035	0.050	0.89	1.27	
Z	0.155		3.93		

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

## **Part Marking System**



Pin Assignment				
1	Cathode			
2	Anode			
3	Gate			
4	Anode			

#### **Ordering Information Device Shipping Package** MCR12DCMT4 DPAK **DPAK** MCR12DCMT4G (Pb-Free) 2500/ Tape & Reel MCR12DCNT4 TO-220AB TO-220AB MCR12DCNT4G (Pb-Free)

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